Protection of the Optical Properties of Few Layer 2D Phosphane

Dylan Renaud^{1,2}, S. Deckoff-Jones³, J. Zhang³, M. Man³ and K. Dani³

¹Dept. of Applied Physics and Mathematics, New Jersey Institute of Technology, Newark, New Jersey, USA ²NanoJapan: International Research Experience for Undergraduates Program, Rice University, Houston, TX, USA ³Dani Femtosecond Spectroscopy Unit, Okinawa Institute of Science and Technology

Graduate University, Onna, Japan

Over the past year, the discovery and development of 2D black phosphorous (2D Phosphane) has generated much excitement due to its high carrier mobility, strong anisotropy, and direct bandgap. 2D phosphane's bandgap exhibits a significant layer dependency allowing for tunability from 0.3 eV (bulk) to 2 eV (monolayer), making it a versatile material for optical applications. The primary issue preventing the integration and development of 2D phosphane is the material's ambient degradation. In the presence of light, water, and oxygen, black phosphorous undergoes a rapid photoassisted oxidation reaction resulting in the destruction of its electronic and optical properties. This project characterizes this ambient degradation by photoluminescence and goes on to demonstrate an effective method of protecting the crystal's optical properties with the use of thin layered hexagonal boron-nitride (h-BN). This project paves the way for the future use of 2D phosphane in a variety of different optical applications and devices.

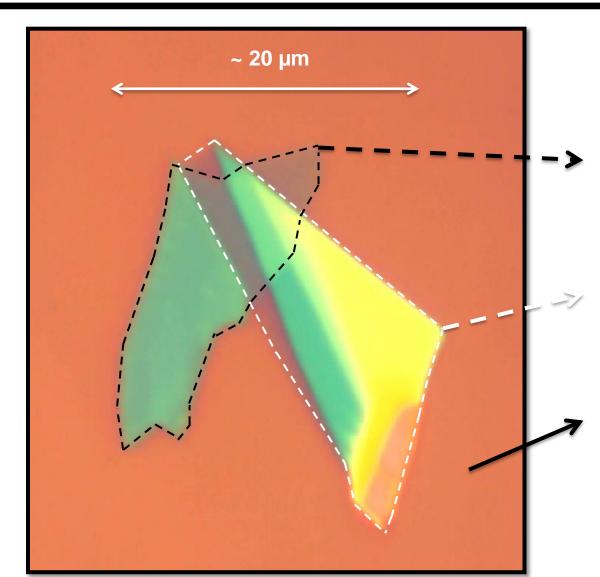


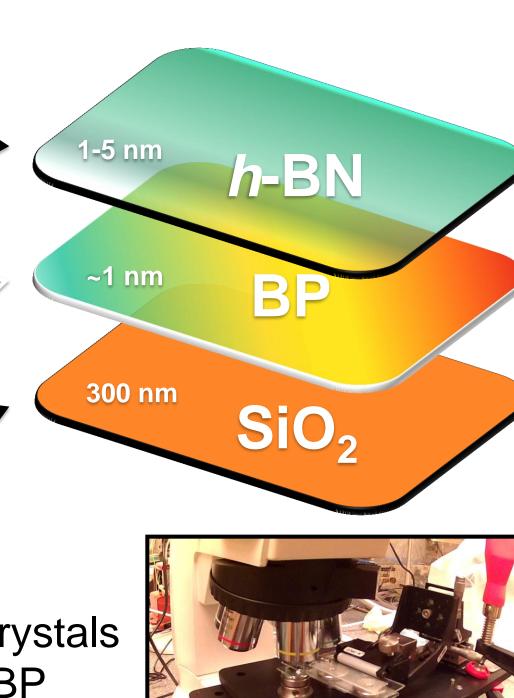


Motive: Black Phosphorous (BP) is an exciting new 2D material with great promise due its extraordinary electrical and optical properties. Unfortunately, BP experiences severe degradation under ambient conditions.

Objective: Develop a method of protecting the crystal such that its photoluminescence is preserved, allowing it to be utilized in future optical projects.

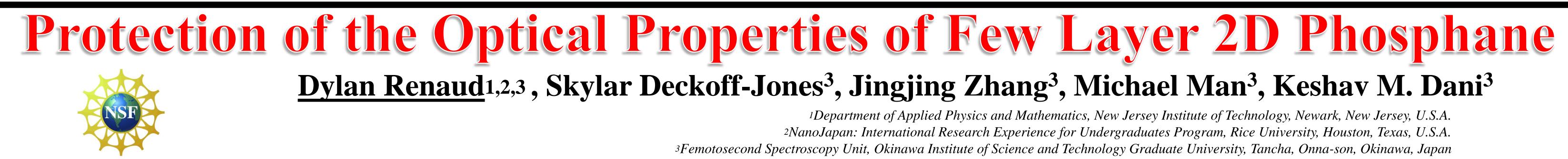
Protection Method



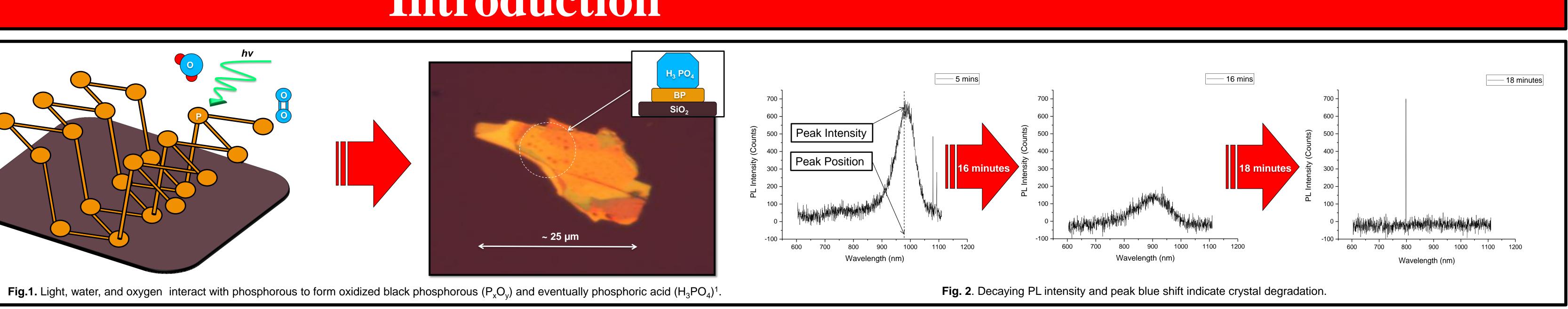


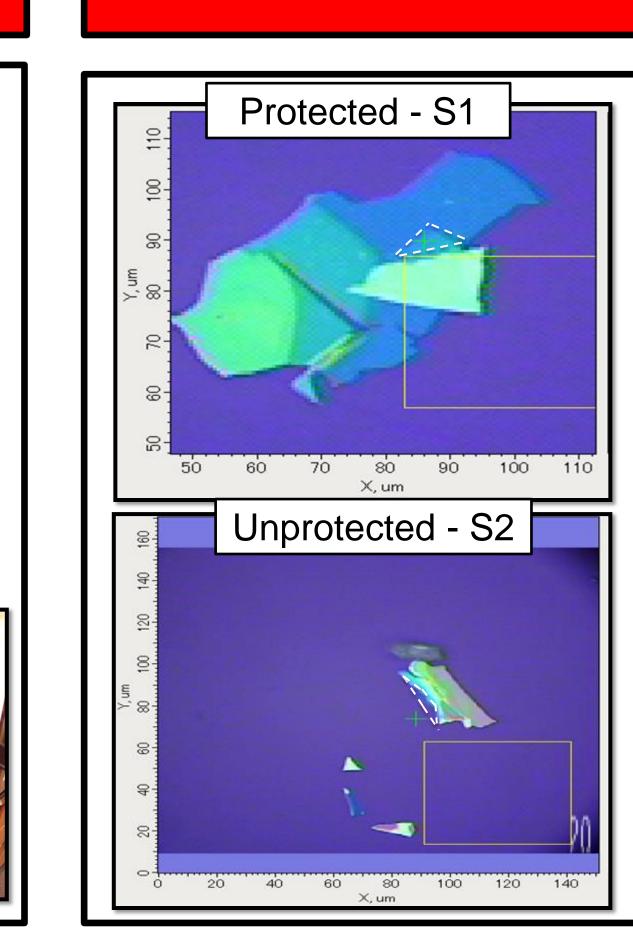
Method: Thin (1-5 nm) *h*-BN crystals are set on bi- and mono-layer BP using viscoelastic stamping and micromanipulator.

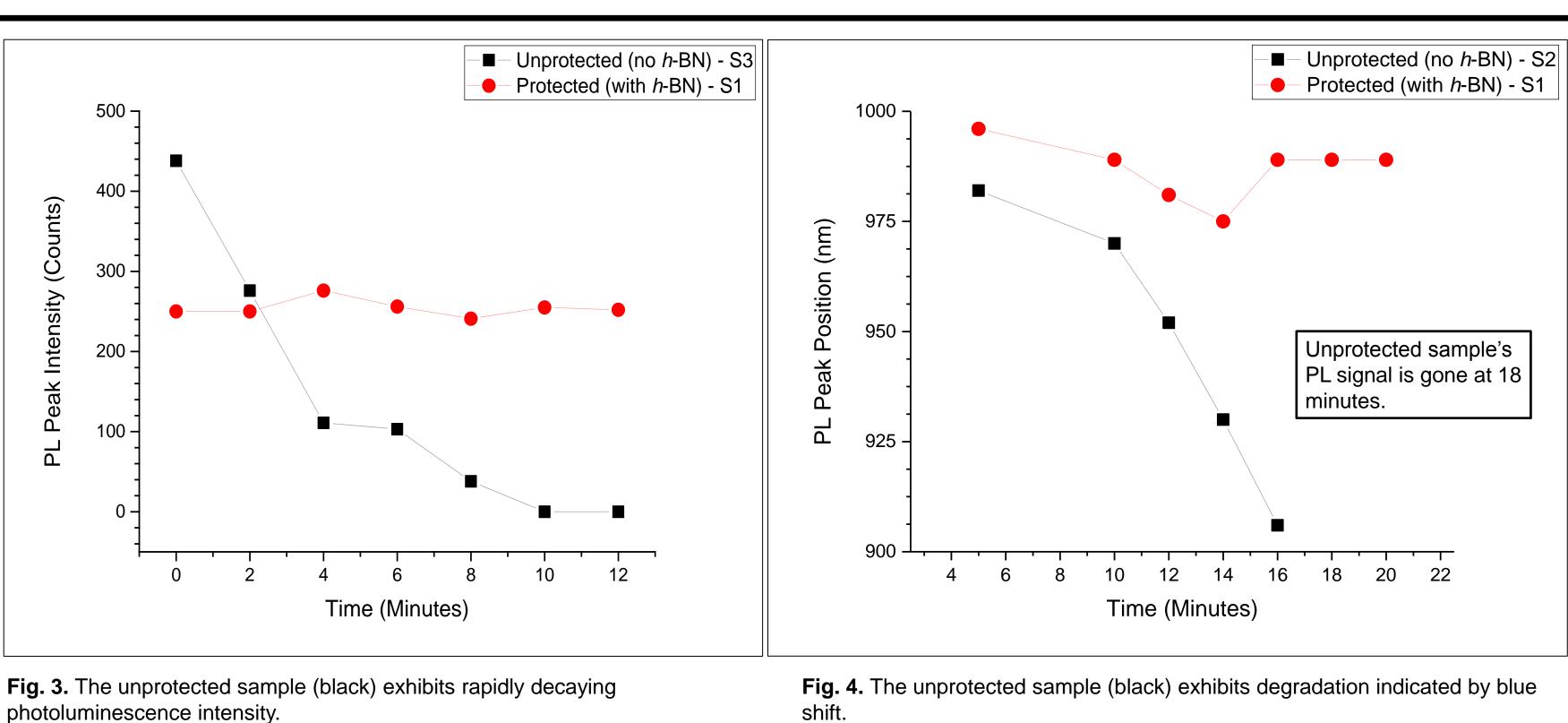
h-BN BP SiO



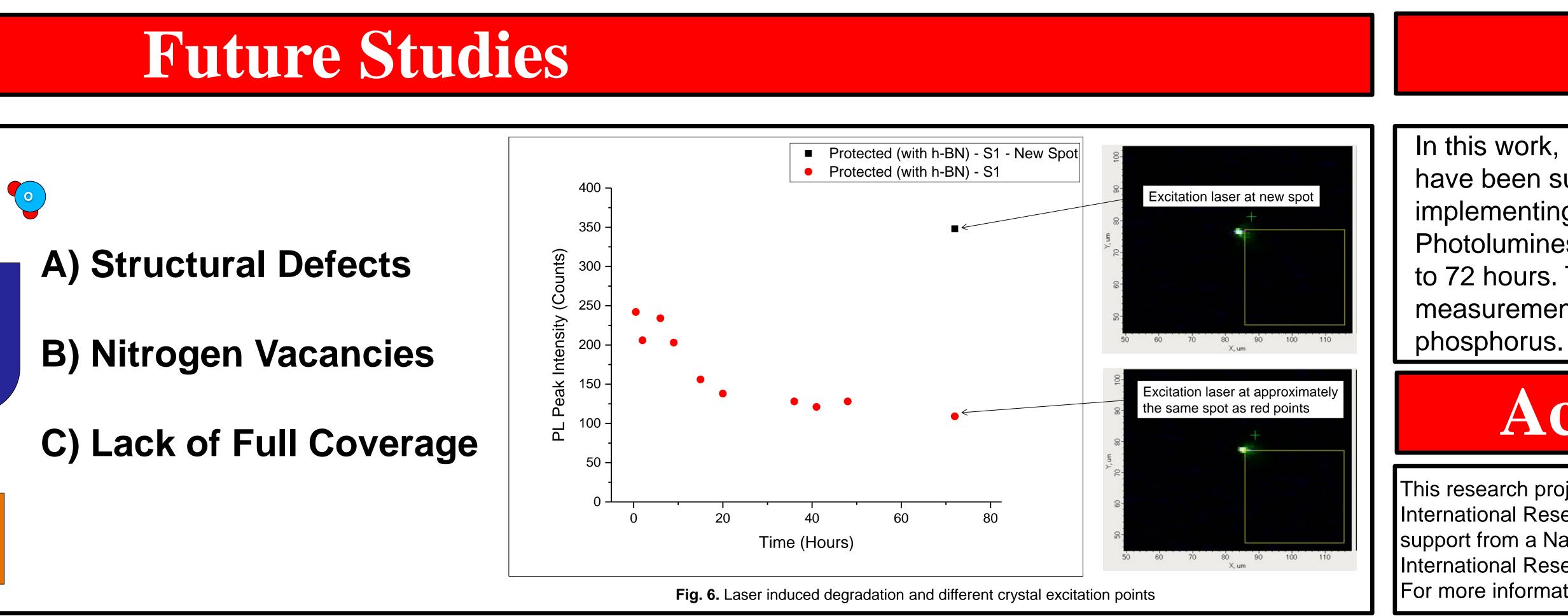
Introduction







photoluminescence intensity.



<u>Dylan Renaud</u>1,2,3, Skylar Deckoff-Jones³, Jingjing Zhang³, Michael Man³, Keshav M. Dani³

¹Department of Applied Physics and Mathematics, New Jersey Institute of Technology, Newark, New Jersey, U.S.A. ²NanoJapan: International Research Experience for Undergraduates Program, Rice University, Houston, Texas, U.S.A.

³Femotosecond Spectroscopy Unit, Okinawa Institute of Science and Technology Graduate University, Tancha, Onna-son, Okinawa, Japan

Results

Protected (with *h*-BN) - S1 1000 975 ĉ Protected (with h-BN 950 925 0 60 120 180 240 300 360 Time (Minutes 900 Time (Hours)

Fig. 5. Long term PL peak position (nm) stability of the *h*-BN protected sample up to 72 hours. Inset is first 6 hours.

Conclusion

In this work, bi-layer black phosphorus crystals have been successfully protected for 24 hr+ by implementing protective layers of *h*-BN. Photoluminescence was measured from samples for up to 72 hours. This work will enable future optical measurements and applications of few layer black

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